

ABSTRACT

SEMICONDUCTOR STRUCTURE AND METHOD FOR PROCESSING SUCH

5

A STRUCTURE

A method for processing a low ohmic contact structure to a buried conductive layer in or below a device layer forming part of a  
10 semiconductor component is presented, whereby first a highly doped region within said device layer reaching said buried conductive layer is realised, this being followed by a step of etching a trench through said highly doped region to a final depth which extends at least to the semiconductor substrate underneath said buried conductive layer. In  
15 a variant method this trench is first pre-etched until a predetermined depth, before the highly doped region is provided.

A semiconductor structure which is realised by these methods is described as well.

20

Fig. 1